

Kyle J Liddy

List of Publications by Year in descending order

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Version: 2024-02-01

10

papers

421

citations

1163117

8

h-index

1588992

8

g-index

10

all docs

10

docs citations

10

times ranked

331

citing authors

#	ARTICLE	IF	CITATIONS
1	$\text{I}^2\text{-Gallium oxide power electronics}$. APL Materials, 2022, 10, .	5.1	184
2	Lateral $\text{I}^2\text{-Ga}_{2}\text{O}_3$ field effect transistors. Semiconductor Science and Technology, 2020, 35, 013002.	2.0	85
3	RF Power Performance of $\text{Sc(Al,Ga)N/GaN HEMTs}$ at Ka-Band. IEEE Electron Device Letters, 2020, 41, 1181-1184.	3.9	41
4	Thin channel $\text{I}^2\text{-Ga}_{2}\text{O}_3$ MOSFETs with self-aligned refractory metal gates. Applied Physics Express, 2019, 12, 126501.	2.4	35
5	Pulsed Power Performance of $\langle i \rangle \text{I}^2 \langle /i \rangle \text{-Ga}_{2}\text{O}_3$ MOSFETs at L-Band. IEEE Electron Device Letters, 2020, 41, 989-992.	3.9	32
6	Toward high voltage radio frequency devices in $\langle i \rangle \text{I}^2 \langle /i \rangle \text{-Ga}_2\text{O}_3$. Applied Physics Letters, 2020, 117, .	3.3	23
7	Thermally-Aware Layout Design of $\langle i \rangle \text{I}^2 \langle /i \rangle \text{-Ga}_{2}\text{O}_3$ Lateral MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 1251-1257.	3.0	11
8	Scaled T-Gate $\langle i \rangle \text{I}^2 \langle /i \rangle \text{-Ga}_{2}\text{O}_3$ MESFETs With 2.45 kV Breakdown and High Switching Figure of Merit. IEEE Electron Device Letters, 2022, 43, 1307-1310.	3.9	8
9	The effectiveness of heat extraction by the drain metal contact of $\text{I}^2\text{-Ga}_2\text{O}_3$ MOSFETs. , 2021, , .		1
10	Towards the Integration of $\text{Hf}_{0.8}\text{Zr}_{0.2}\text{O}_2$ -based Negative Capacitance Dielectrics on Ga_{2}O_3 Substrates. , 2021, , .		1